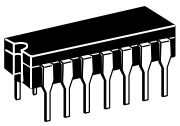
MC14077B — See Page 6-160
MC14078B, MC14081B, MC14082B — See Page 6-5

MC14093B

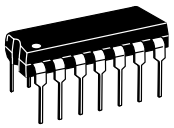
Quad 2-Input "NAND" Schmitt Trigger

The MC14093B Schmitt trigger is constructed with MOS P–channel and N–channel enhancement mode devices in a single monolithic structure. These devices find primary use where low power dissipation and/or high noise immunity is desired. The MC14093B may be used in place of the MC14011B quad 2–input NAND gate for enhanced noise immunity or to "square up" slowly changing waveforms.

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low–Power TTL Loads or One Low–Power Schottky TTL Load Over the Rated Temperature Range
- Triple Diode Protection on All Inputs
- Pin–for–Pin Compatible with CD4093
- Can be Used to Replace MC14011B
- Independent Schmitt–Trigger at each Input



L SUFFIX
CERAMIC
CASE 632



P SUFFIX
PLASTIC
CASE 646

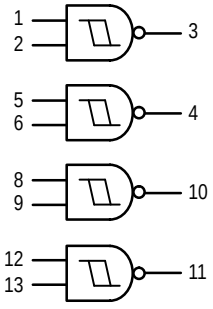
D SUFFIX
SOIC
CASE 751A

ORDERING INFORMATION

MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBD	SOIC

T_A = – 55° to 125°C for all packages.

LOGIC DIAGRAM



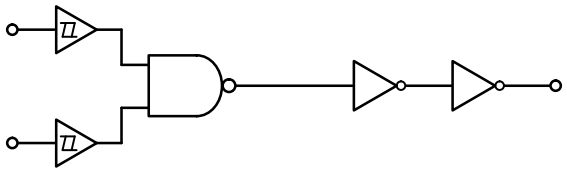
V_{DD} = PIN 14
V_{SS} = PIN 7

MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	– 0.5 to + 18.0	V
V_{in}, V_{out}	Input or Output Voltage (DC or Transient)	– 0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient), per Pin	± 10	mA
P_D	Power Dissipation, per Package†	500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating:
Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C
Ceramic "L" Packages: – 12 mW/°C From 100°C To 125°C

EQUIVALENT CIRCUIT SCHEMATIC
(1/4 OF CIRCUIT SHOWN)



This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

REV 3
1/94

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ #	25°C Max	125°C Min	125°C Max	Unit
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	— — —	0.05 0.05 0.05	— — —	0 0 0	0.05 0.05 0.05	— — —	0.05 0.05 0.05	Vdc
"1" Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	— — —	4.95 9.95 14.95	5.0 10 15	— — —	4.95 9.95 14.95	— — —	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	 5.0 5.0 10 15	 – 3.0 – 0.64 – 1.6 – 4.2	 — — — —	 – 2.4 – 0.51 – 1.3 – 3.4	 – 4.2 – 0.88 – 2.25 – 8.8	 — — — —	 – 1.7 – 0.36 – 0.9 – 2.4	 — — — —	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	— — —	0.51 1.3 3.4	0.88 2.25 8.8	— — —	0.36 0.9 2.4	— — —	mAdc
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	— — —	0.25 0.5 1.0	— — —	0.0005 0.0010 0.0015	0.25 0.5 1.0	— — —	7.5 15 30	µAdc
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (1.2 µA/kHz) f + I_{DD} I_T = (2.4 µA/kHz) f + I_{DD} I_T = (3.6 µA/kHz) f + I_{DD}							µAdc
Hysteresis Voltage	V_H†	5.0 10 15	0.3 1.2 1.6	2.0 3.4 5.0	0.3 1.2 1.6	1.1 1.7 2.1	2.0 3.4 5.0	0.3 1.2 1.6	2.0 3.4 5.0	Vdc
Threshold Voltage Positive–Going	V_{T+}	5.0 10 15	2.2 4.6 6.8	3.6 7.1 10.8	2.2 4.6 6.8	2.9 5.9 8.8	3.6 7.1 10.8	2.2 4.6 6.8	3.6 7.1 10.8	Vdc
Negative–Going	$V_{T–}$	5.0 10 15	0.9 2.5 4.0	2.8 5.2 7.4	0.9 2.5 4.0	1.9 3.9 5.8	2.8 5.2 7.4	0.9 2.5 4.0	2.8 5.2 7.4	Vdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

** The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.004.

SWITCHING CHARACTERISTICS (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ #	Max	Unit
Output Rise Time	t_{TLH}	5.0 10 15	— — —	100 50 40	200 100 80	ns
Output Fall Time	t_{THL}	5.0 10 15	— — —	100 50 40	200 100 80	ns
Propagation Delay Time	t_{PLH}, t_{PHL}	5.0 10 15	— — —	125 50 40	250 100 80	ns

#Data labeled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

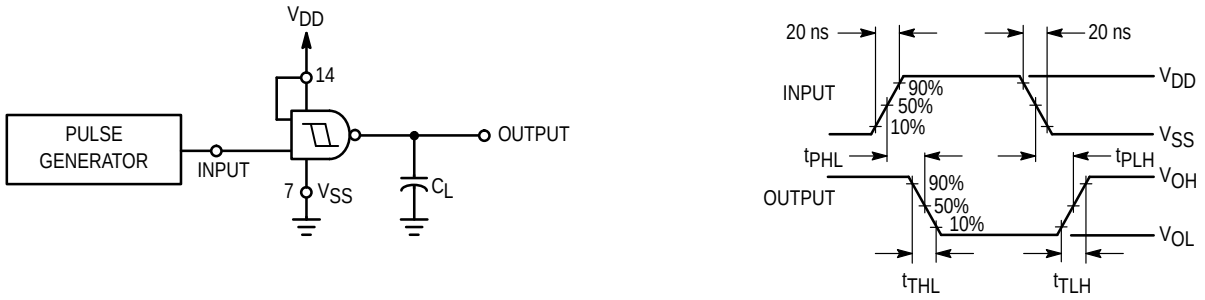
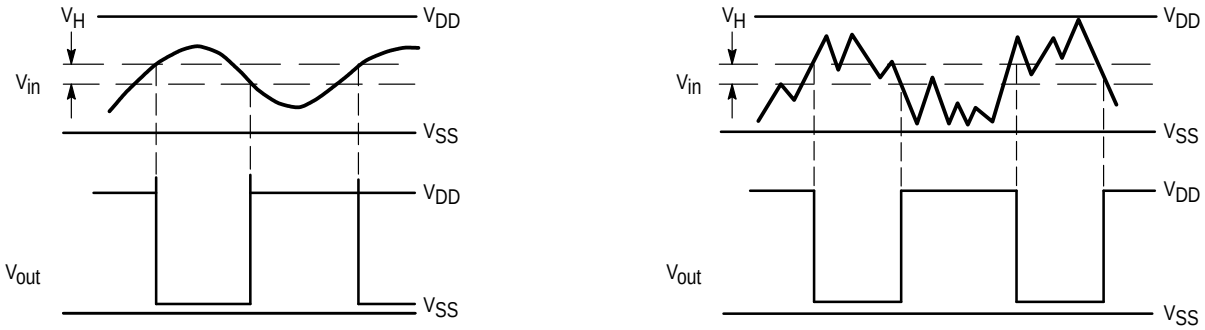


Figure 1. Switching Time Test Circuit and Waveforms



(a) Schmitt Triggers will square up inputs with slow rise and fall times.

(b) A Schmitt trigger offers maximum noise immunity in gate applications.

Figure 2. Typical Schmitt Trigger Applications

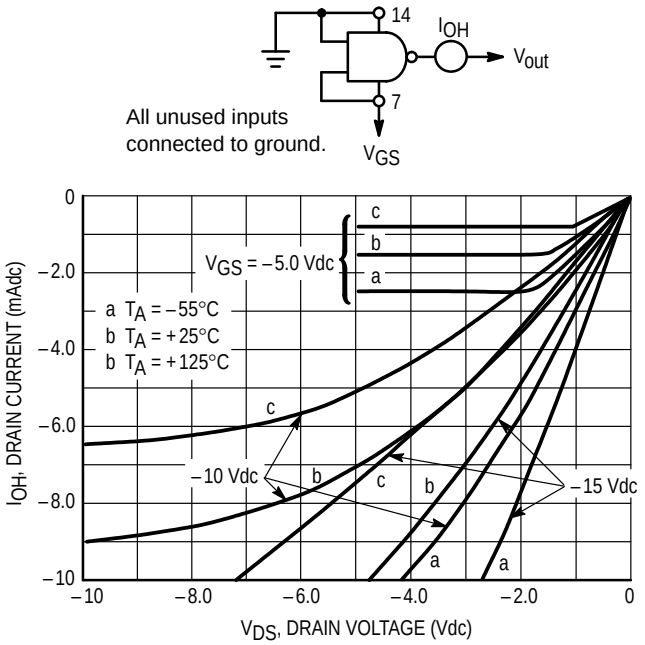


Figure 3. Typical Output Source Characteristics Test Circuit

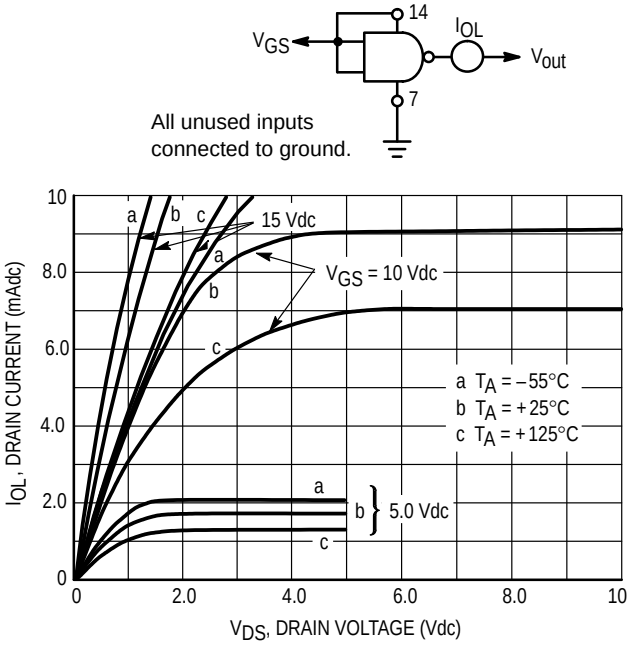


Figure 4. Typical Output Sink Characteristics Test Circuit

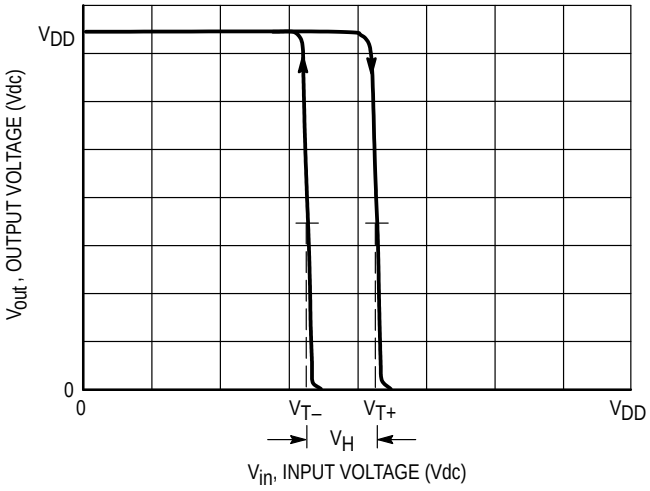
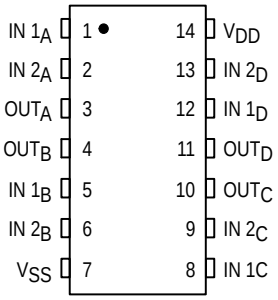


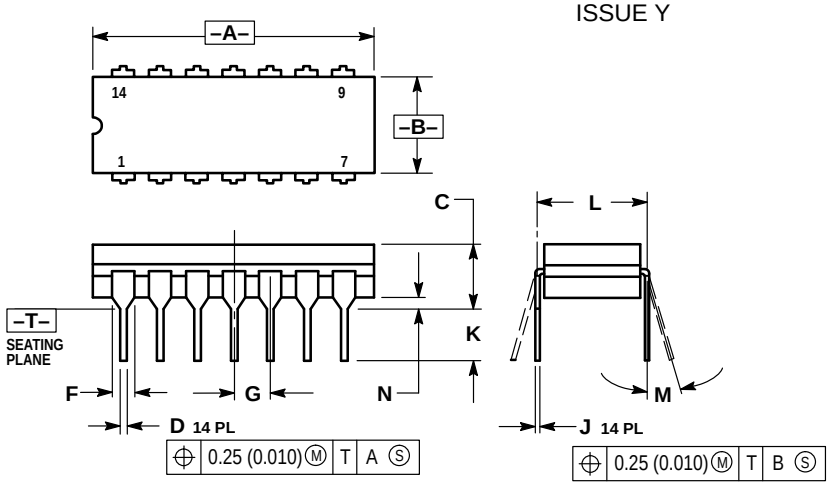
Figure 5. Typical Transfer Characteristics

PIN ASSIGNMENT



OUTLINE DIMENSIONS

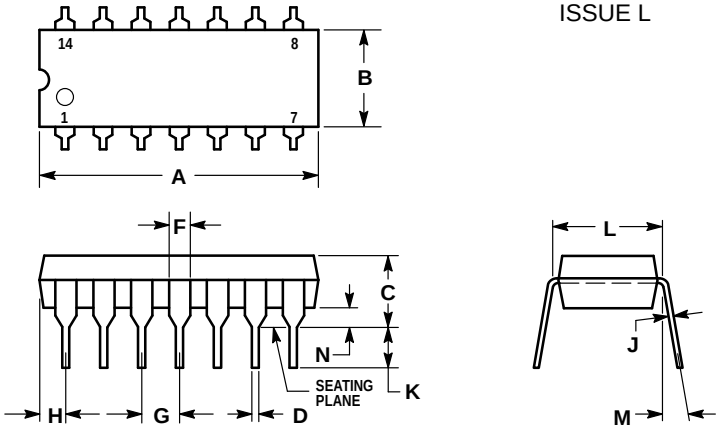
L SUFFIX
CERAMIC DIP PACKAGE
CASE 632–08
ISSUE Y



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.94
B	0.245	0.280	6.23	7.11
C	0.155	0.200	3.94	5.08
D	0.015	0.020	0.39	0.50
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

P SUFFIX
PLASTIC DIP PACKAGE
CASE 646–06
ISSUE L

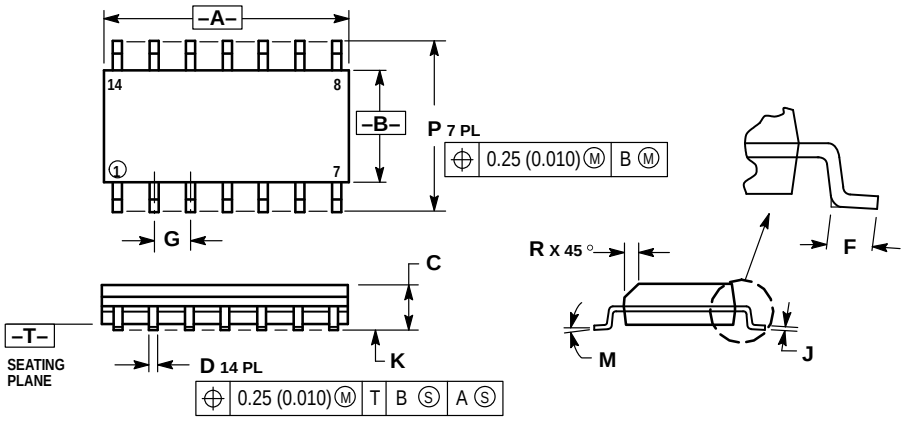


NOTES:
1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
4. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62 BSC	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

OUTLINE DIMENSIONS

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751A–03
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

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